

# PSMN1R7-30YL

# N-channel 30 V 1.7 mΩ logic level MOSFET in LFPAK

Rev. 1 — 30 May 2011

**Product data sheet** 

### 1. Product profile

### 1.1 General description

Logic level N-channel MOSFET in LFPAK package qualified to 175 °C. This product is designed and qualified for use in a wide range of industrial, communications and domestic equipment.

### 1.2 Features and benefits

- Advanced TrenchMOS provides low RDSon and low gate charge
- High efficiency gains in switching power convertors
- Improved mechanical and thermal characteristics
- LFPAK provides maximum power density in a Power SO8 package

### 1.3 Applications

- DC-to-DC converters
- Lithium-ion battery protection
- Load switching

- Motor control
- Server power supplies

#### 1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
$V_{DS}$	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C		-	-	30	V
I <sub>D</sub>	drain current	$T_{mb}$ = 25 °C; $V_{GS}$ = 10 V; see <u>Figure 1</u>	[1]	-	-	100	Α
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; see <u>Figure 2</u>		-	-	109	W
Tj	junction temperature			-55	-	175	°C
Static char	acteristics						
R <sub>DSon</sub>	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 15 \text{ A};$ $T_j = 100 \text{ °C}; \text{ see } \frac{\text{Figure } 13}{}$		-	-	2.4	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 15 \text{ A};$ $T_j = 25 \text{ °C}$		-	1.3	1.7	mΩ
Dynamic c	haracteristics						
$Q_{GD}$	gate-drain charge	$V_{GS}$ = 4.5 V; $I_D$ = 10 A; $V_{DS}$ = 12 V; see <u>Figure 14</u> ; see <u>Figure 15</u>		-	8.7	-	nC



Table 1. Quick reference data ...continued

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Q <sub>G(tot)</sub>	total gate charge	$V_{GS} = 4.5 \text{ V}; I_D = 10 \text{ A};$ $V_{DS} = 12 \text{ V}; \text{ see } \frac{\text{Figure } 14}{\text{ Figure } 14}$	-	36.2	-	nC
Avalanche	ruggedness					
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy	$V_{GS}$ = 10 V; $T_{j(init)}$ = 25 °C; $I_D$ = 100 A; $V_{sup}$ ≤ 30 V; $R_{GS}$ = 50 Ω; unclamped	-	-	241	mJ

<sup>[1]</sup> Continuous current is limited by package.

### 2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	source		
2	S	source	mb	D
3	S	source		
4	G	gate	[Q]	
mb	D	mounting base; connected to drain	1 2 3 4	mbb076 S

SOT669 (LFPAK; Power-SO8)

### 3. Ordering information

Table 3. Ordering information

Type number	Package				
	Name	Description	Version		
PSMN1R7-30YL	LFPAK; Power-SO8	plastic single-ended surface-mounted package; 4 leads	SOT669		

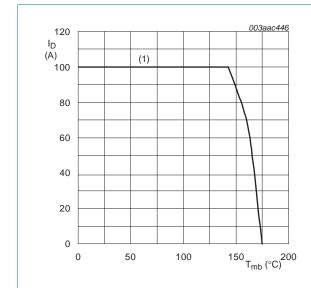
### 4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

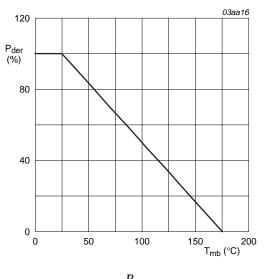
Symbol	Parameter	Conditions		Min	Max	Unit
$V_{DS}$	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C		-	30	V
$V_{DSM}$	peak drain-source voltage	$t_p \le 25 \text{ ns}$ ; f $\le 500 \text{ kHz}$ ; $E_{DS(AL)} \le 360 \text{ nJ}$ ; pulsed		-	35	V
$V_{DGR}$	drain-gate voltage	$T_j \ge 25$ °C; $T_j \le 175$ °C; $R_{GS} = 20$ kΩ		-	30	V
$V_{GS}$	gate-source voltage			-20	20	V
$I_D$	drain current	$V_{GS} = 10 \text{ V}; T_{mb} = 100 \text{ °C}; \text{ see } \frac{\text{Figure 1}}{\text{Model}}$	[1]	-	100	Α
		$V_{GS} = 10 \text{ V}; T_{mb} = 25 \text{ °C}; \text{ see } \frac{\text{Figure 1}}{\text{Model}}$	[1]	-	100	Α
$I_{DM}$	peak drain current	pulsed; $t_p \le 10 \mu s$ ; $T_{mb} = 25 ^{\circ}C$ ; see Figure 3		-	790	Α
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; see <u>Figure 2</u>		-	109	W
T <sub>stg</sub>	storage temperature			-55	175	°C
Tj	junction temperature			-55	175	°C
Source-drain	diode					
Is	source current	T <sub>mb</sub> = 25 °C	[1]	-	100	Α
I <sub>SM</sub>	peak source current	pulsed; $t_p \le 10 \ \mu s$ ; $T_{mb} = 25 \ ^{\circ}C$		-	790	Α
Avalanche ru	ggedness					
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy	$V_{GS}$ = 10 V; $T_{j(init)}$ = 25 °C; $I_{D}$ = 100 A; $V_{sup}$ ≤ 30 V; $R_{GS}$ = 50 Ω; unclamped		-	241	mJ

#### [1] Continuous current is limited by package.



 $V_{GS} \ge$  10 V; (1) Capped at 100 A due to package

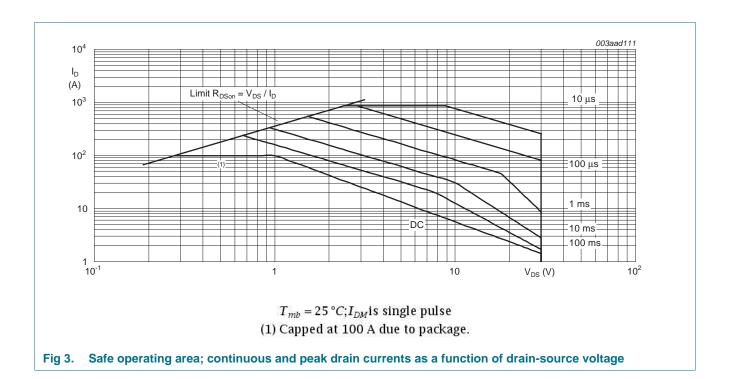
Fig 1. Continuous drain current as a function of mounting base temperature



$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100\%$$

Fig 2. Normalized total power dissipation as a function of mounting base temperature

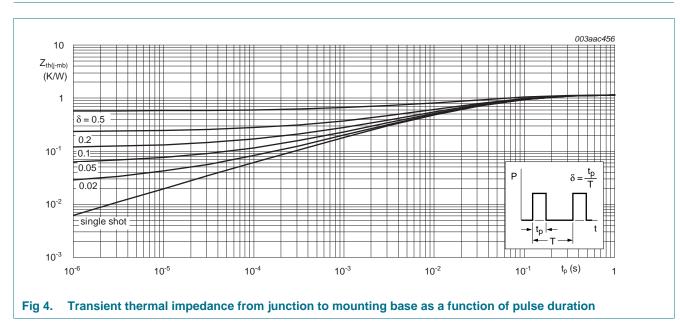
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### 5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	see Figure 4	-	0.5	1.1	K/W



### 6. Characteristics

Table 6. Characteristics

Tested to JEDEC standards where applicable.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	cteristics					
V <sub>(BR)DSS</sub>	drain-source breakdown	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 °C$	30	-	-	V
	voltage	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = -55 °C$	27	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 1$ mA; $V_{DS} = V_{GS}$ ; $T_j = 25$ °C; see <u>Figure 11</u> ; see <u>Figure 12</u>	1.3	1.7	2.15	V
		$I_D$ = 1 mA; $V_{DS}$ = $V_{GS}$ ; $T_j$ = 150 °C; see Figure 12	0.65	-	-	V
		$I_D$ = 1 mA; $V_{DS}$ = $V_{GS}$ ; $T_j$ = -55 °C; see <u>Figure 12</u>	-	-	2.45	V
I <sub>DSS</sub>	drain leakage current	$V_{DS} = 30 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	1	μΑ
		$V_{DS} = 30 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 150 \text{ °C}$	-	-	100	μΑ
I <sub>GSS</sub>	gate leakage current	$V_{GS} = 16 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	100	nΑ
		$V_{GS} = -16 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	100	nΑ
R <sub>DSon</sub>	drain-source on-state	$V_{GS} = 4.5 \text{ V}; I_D = 15 \text{ A}; T_j = 25 \text{ °C}$	-	1.8	2.1	mΩ
	resistance	$V_{GS} = 10 \text{ V}; I_D = 15 \text{ A}; T_j = 150 \text{ °C};$ see <u>Figure 13</u>	-	-	2.8	mΩ
	$V_{GS} = 10 \text{ V}; I_D = 15 \text{ A}; T_j = 100 \text{ °C};$ see Figure 13	-	-	2.4	mΩ	
		$V_{GS} = 10 \text{ V}; I_D = 15 \text{ A}; T_j = 25 \text{ °C}$	-	1.3	1.7	mΩ
$R_{G}$	gate resistance	f = 1 MHz	-	0.77	1.5	Ω
Dynamic ch	aracteristics					
Q <sub>G(tot)</sub> total gate	total gate charge	$I_D = 10 \text{ A}$ ; $V_{DS} = 12 \text{ V}$ ; $V_{GS} = 10 \text{ V}$ ; see Figure 14; see Figure 15	-	77.9	-	nC
		$I_D = 0 \text{ A}; V_{DS} = 0 \text{ V}; V_{GS} = 10 \text{ V}$	-	70	-	nC
		$I_D = 10 \text{ A}$ ; $V_{DS} = 12 \text{ V}$ ; $V_{GS} = 4.5 \text{ V}$ ; see Figure 14	-	36.2	-	nC
$Q_{GS}$	gate-source charge	$I_D = 10 \text{ A}; V_{DS} = 12 \text{ V}; V_{GS} = 4.5 \text{ V};$	-	11.6	-	nC
Q <sub>GS(th)</sub>	pre-threshold gate-source charge	see <u>Figure 14</u> ; see <u>Figure 15</u>	-	8	-	nC
Q <sub>GS(th-pl)</sub>	post-threshold gate-source charge		-	3.6	-	nC
$Q_{GD}$	gate-drain charge		-	8.7	-	nC
V <sub>GS(pl)</sub>	gate-source plateau voltage	V <sub>DS</sub> = 12 V; see <u>Figure 14</u> ; see <u>Figure 15</u>	-	2.34	-	V
C <sub>iss</sub>	input capacitance	$V_{DS} = 12 \text{ V}; V_{GS} = 0 \text{ V}; f = 1 \text{ MHz};$	-	5057	-	pF
C <sub>oss</sub>	output capacitance	T <sub>j</sub> = 25 °C; see <u>Figure 16</u>	-	1082	-	pF
C <sub>rss</sub>	reverse transfer capacitance		-	398	-	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS} = 12 \text{ V}; R_L = 0.5 \Omega; V_{GS} = 4.5 \text{ V};$	-	46	-	ns
t <sub>r</sub>	rise time	$R_{G(ext)} = 4.7 \Omega$	-	72	-	ns
t <sub>d(off)</sub>	turn-off delay time		-	76	-	ns
t <sub>f</sub>	fall time		-	34	-	ns

 Table 6.
 Characteristics ...continued

Tested to JEDEC standards where applicable.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit	
Source-drai	Source-drain diode						
$V_{SD}$	source-drain voltage	$I_S = 25 \text{ A}$ ; $V_{GS} = 0 \text{ V}$ ; $T_j = 25 \text{ °C}$ ; see Figure 17	-	0.78	1.2	V	
t <sub>rr</sub>	reverse recovery time	$I_S = 20 \text{ A}$ ; $dI_S/dt = -100 \text{ A/}\mu\text{s}$ ;	-	45	-	ns	
Q <sub>r</sub>	recovered charge	$V_{GS} = 0 \text{ V}; V_{DS} = 20 \text{ V}$	-	56	-	nC	

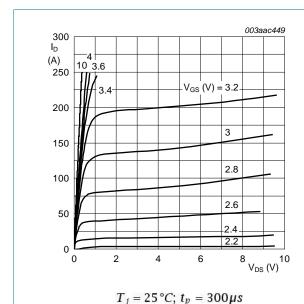


Fig 5. Output characteristics: drain current as a function of drain-source voltage; typical values

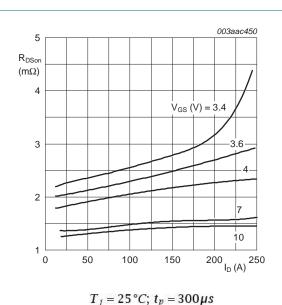


Fig 6. Drain-source on-state resistance as a function of drain current; typical values

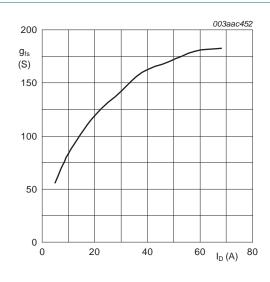
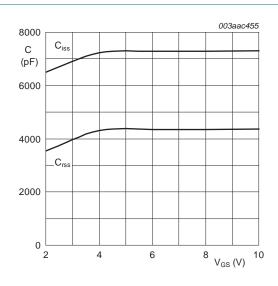


Fig 7. Forward transconductance as a function of drain current; typical values

 $T_j = 25 \,^{\circ}C; V_{DS} = 15 \, V$ 

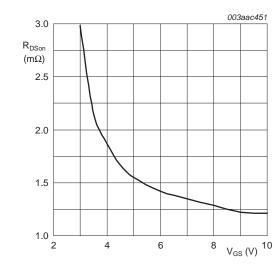


 $V_{DS} = 0V; f = 1MHz$ 

Fig 8. Input and reverse transfer capacitances as a function of gate-source voltage; typical values

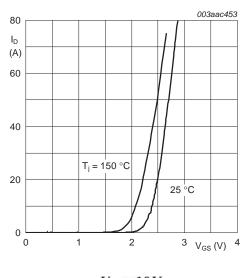
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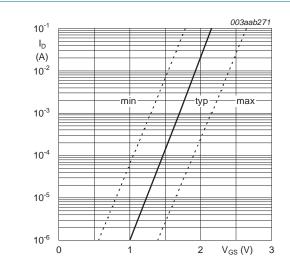
 $T_j = 25\,^{\circ}C; I_D = 15A$ 

Fig 9. Drain-source on-state resistance as a function of gate-source voltage; typical values



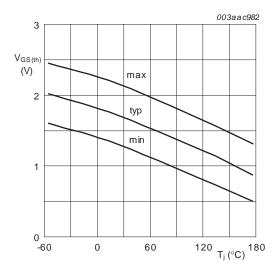
 $V_{DS} = 10 V$ 

Fig 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values



 $T_j = 25 \,{}^{\circ}C; V_{DS} = 5V$ 

Fig 11. Sub-threshold drain current as a function of gate-source voltage



 $I_D = 1mA; V_{DS} = V_{GS}$ 

Fig 12. Gate-source threshold voltage as a function of junction temperature

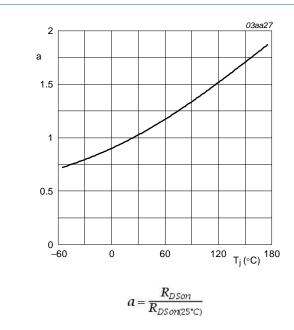


Fig 13. Normalized drain-source on-state resistance factor as a function of junction temperature

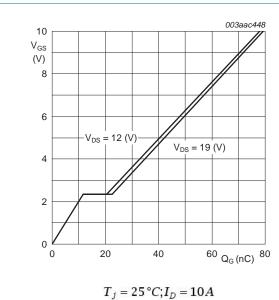


Fig 15. Gate-source voltage as a function of gate charge; typical values

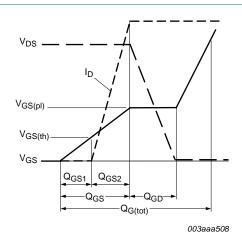
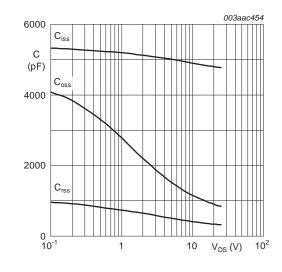


Fig 14. Gate charge waveform definitions



 $V_{GS}=0\,V; f=1MHz$ 

Fig 16. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

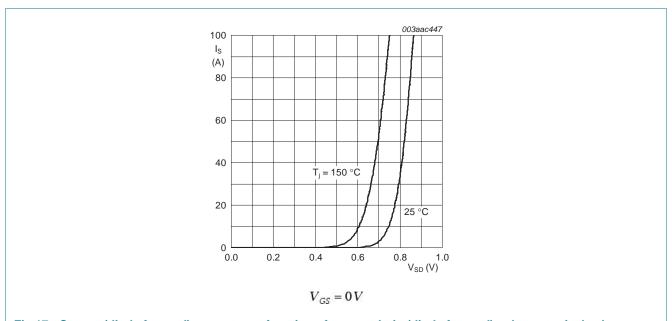
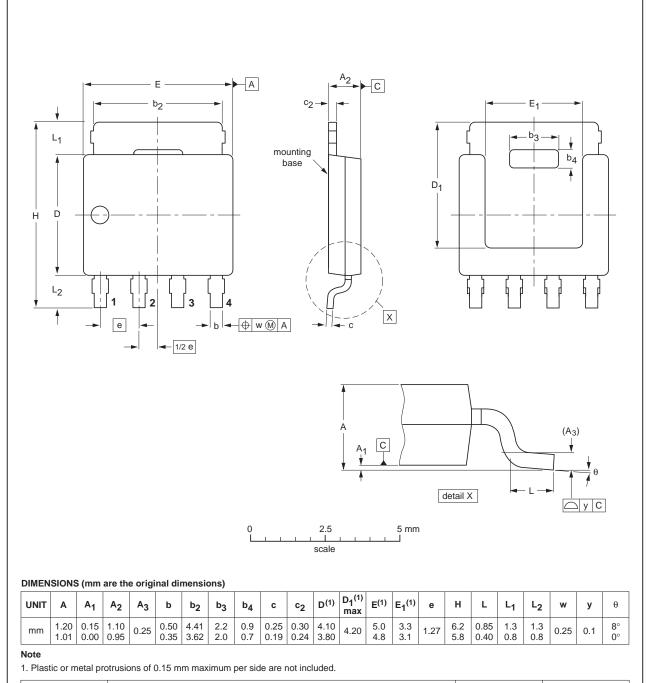


Fig 17. Source (diode forward) current as a function of source-drain (diode forward) voltage; typical values

### 7. Package outline

### Plastic single-ended surface-mounted package (LFPAK; Power-SO8); 4 leads

**SOT669** 



OUTLINE	REFERENCES			FERENCES EUROPEAN		ISSUE DATE
VERSION	IEC	JEDEC	JEITA		PROJECTION	1330E DATE
SOT669		MO-235				<del>06-03-16</del> 11-03-25

Fig 18. Package outline SOT669 (LFPAK; Power-SO8)

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## 8. Revision history

#### Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes		
PSMN1R7-30YL v.5	20110530	Product data sheet	-	PSMN1R7-30YL v.4		
Modifications: • Various changes to content.						
PSMN1R7-30YL v.4	20100420	Product data sheet	-	PSMN1R7-30YL v.3		

### 9. Legal information

#### 9.1 Data sheet status

Document status [1] [2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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# PSMN1R7-30YL

### **Nexperia**

### N-channel 30 V 1.7 mΩ logic level MOSFET in LFPAK

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